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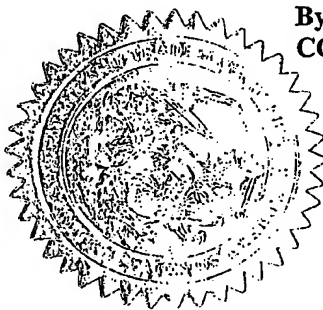
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PROVISIONAL APPLICATION FOR PATENT COVER SHEET

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TITLE OF THE INVENTION (500 characters max)					
METHOD FOR ELECTROPOLISHING METAL FILM ON SUBSTRATE					
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ENCLOSED APPLICATION PARTS (check all that apply)					
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<input checked="" type="checkbox"/> Application Data Sheet. See 37 CFR 1.76					
METHOD OF PAYMENT OF FILING FEES FOR THIS PROVISIONAL APPLICATION FOR PATENT					
<input checked="" type="checkbox"/> Applicant claims small entity status. See 37 CFR 1.27.				FILING FEE AMOUNT (\$)	
<input checked="" type="checkbox"/> A check or money order is enclosed to cover the filing fees				Filing Fee Amount (\$)	
<input type="checkbox"/> The Commissioner is hereby authorized to charge filing fees or credit any overpayment to Deposit Account Number: <input type="text"/>				\$80.00	
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The invention was made by an agency of the United States Government or under a contract with an agency of the United States Government.					
<input checked="" type="checkbox"/> No					
<input type="checkbox"/> Yes, the name of the U.S. Government agency and the Government contract number are <input type="text"/>					

Respectfully submitted,

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07/22/02

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USE ONLY FOR FILING A PROVISIONAL APPLICATION FOR PATENT

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Application Data Sheet**Application Information**

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METHOD FOR ELECTROPOLISHING METAL FILM ON SUBSTRATE

Objectives:

This present invention relates generally to a method to provide better and precise control of the end point detection in electropolishing.

Descriptions:

Fig. 1 shows one embodiment of nozzle plate for wafer electropolishing module which was previously disclosed in U.S. Patent No. 6,248,222 B1, entitled METHODS AND APPARATUS FOR HOLDING AND POSITIONING SEMICONDUCTOR WORKPIECES DURING ELECTROPOLISHING AND/OR ELECTROPLATING OF THE WORKPIECES, dated June 19, 2001, and Provisional Application Serial No. 60/372, 566, entitled METHOD AND APPARATUS FOR ELECTROPOLISHING AND/OR ELECTROPLATING, filed on April 14, 2002, the entire content of which are incorporated herein by reference.

As shown in Fig. 1, nozzle plate 1004 can include nozzles 1008, 1010 and end-point detector 1006.

For a more detailed discussion of end point detection, see U.S. Patent Serial No. 09/570,566, entitled METHOD AND APPARATUS FOR END-POINT DETECTION, filed on May 12, 2000, which is incorporated in its entirety by reference herein.

Wafers from the same deposition recipe will generally have a similar metal film thickness profile and consequently can be polished using a similar polishing recipe. A recipe can consist of liquid flow rate, current or voltage set-point, center-to-edge distance, initial rotational speed, polishing duration, center polishing rotational speed, nozzle type, current or voltage table, bulk ratio table for constant current, and repetition setting.

Typically, before wafers 1002 are polished in accordance with the present invention, a substrate thickness metrology tool will measure and map the thickness of the film deposited on said wafers. The measurements can consist of radius, theta, and relative thickness of the fixed locations. As shown in Fig. 2A, the metrology tool can measure multiple fixed locations 2010 to map the relative thickness of wafer 1002.

Polish the Top Portion of Copper Layer.

As nozzle 1008 or 1010 is at position 2022 (x, y), the present invention will reference the thickness measurement data based on points closest to 2022 (x, y). As shown in Figs. 2A, 2B and 2C, a particular embodiment of a substrate thickness at point 2022 (x, y) can be interpolated based on four-points locations 2012 (x_i, y_{j+1}), 2014 (x_{i+1}, y_{j+1}), 2016 (x_{i+1}, y_j), 2018 (x_i, y_j). The thickness of film at location 2022 (x, y) can be as assumed as:

$$T = Ax + By + Cxy + D \quad (1)$$

where the interpolate value thickness T at (x, y) from the following four known points is:

$$T_{i,j} \text{ at } (x_i, y_j) \quad T_{i,j+1} \text{ at } (x_i, y_{j+1})$$

$$T_{i+1,j} \text{ at } (x_{i+1}, y_j) \quad T_{i+1,j+1} \text{ at } (x_{i+1}, y_{j+1})$$

$$T_{i,j} = Ax_i + By_j + Cx_i y_j + D \quad (2)$$

$$T_{i,j+1} = Ax_i + By_{j+1} + Cx_i y_{j+1} + D \quad (3)$$

$$T_{i+1,j} = Ax_{i+1} + By_j + Cx_{i+1} y_j + D \quad (4)$$

$$T_{i+1,j+1} = Ax_{i+1} + By_{j+1} + C \quad (5)$$

The values of A, B, C, and D can be obtained by solving above four equations.

$$C = (T_{ij} - T_{ij+1} - T_{i+1,j} + T_{i+1,j+1}) / [(x_i - x_{i+1}) * (y_j - y_{j+1})]$$

$$B = (T_{ij} - T_{ij+1}) / (y_j - y_{j+1}) - x_i * D$$

$$A = (T_{ij} - T_{i+1,j}) / (x_i - x_{i+1}) - y_j * D$$

$$D = T_{ij} - x_i * B - y_j * [(T_{ij} - T_{ij+1}) / (y_j - y_{j+1})]$$

For more accurate interpolation:

$$T = Ax^2 + By^2 + Cxy + Dx + Ey + F \quad (6)$$

where the Thickness T at (x, y) can be interpolated using six points closest 2022 (x, y) and the constants A, B, C, D, E and F can be obtained by solving the six equations above.

After thickness metal film is calculated by using formula (1) or (6), then computer will calculate the polishing current I based on the thickness as follows:

$$I = k T(x, y) \quad (7)$$

where k is the factor related to polishing rate.

Then computer will send new set point of the polishing current to polishing power supply to perform metal polishing process.

Even in the best of computing environment, there will be delay Δt from the time when above calculation is done to the time when the polishing power supply sent new polishing current to nozzle to polishing 2022 (x, y) . As such the present invention use the delay time Δt as offset time, i.e. at the time Δt before nozzle reaches the point 2022, computer start to calculate the process for point 2022. By this way, the right polishing current for point 2022 will be provided on nozzle just when the nozzle reaches point 2022.

Polish the Remaining Portion of Copper Layer.

After the top portion of copper is removed, more specifically speaking, after remaining metal thickness reaches less than 1000 Å, end-point detector 1006 scans and records the reflectivity of wafer 1002, then metal thickness can be calculated by the following formula:

$$T(x, y) = p(T) * R(x, y) \quad (8)$$

where $R(x, y)$ is the reflectivity of metal film at position 2022 (x, y) measured by end point detector 1006, and $p(T)$ is the conversion factor of reflectivity to thickness, which itself is a function of thickness. $p(T)$ can be measured by using a set of metal film with different thickness, and then store into computer in a form of look-up table. By this way, the thickness $T(x, y)$ can be determined based on look-up table and measured reflectivity. The thickness matrix will be stored in computer memory as follows:

$$\begin{matrix} T_{1,1} & T_{1,2} & T_{1,3} & \dots & T_{1,m} \\ T_{2,1} & T_{2,2} & T_{2,3} & \dots & T_{2,m} \\ T_{3,1} & T_{3,2} & T_{3,3} & \dots & T_{3,m} \\ \dots & & & & \\ T_{n,1} & T_{n,2} & T_{n,3} & \dots & T_{n,m} \end{matrix}$$

Use the similar method as described earlier, the thickness of metal film at any location can be calculated by using formula (1) or (6). Also used in the same way as described before, the polishing current can calculate by using formula (7).

The process is repeated until the reflectivity recorded by end-point detector 1006 is within a pre-set range for the device wafer. It should be mentioned that the pre-set range of reflectivity depends on metal pattern density, and over-polishing range. Usually, the less patterned density, the lower pre-set of reflectivity. Also, the preset reflectivity can vary based on pattern density. As previously disclosed in U.S. Patent Application No. 09/570,566, entitled METHOD AND APPARATUS FOR END-POINT DETECTION,

filed on May 12, 2000, the entire content of which is incorporated herein by reference, the preset reflectivity can be calculated based on pattern density of mask or measured by one polished wafer with minimum metal recess.

As shown in Fig. 3, the control system 3002 that performs the recipe, record the reflectivity, and update the metal film thickness profile will be required to handle the same sets of tasks for one or more wafer electro-polishing modules 3004 simultaneously. The processing and computing load required can slow down the response time for read-outs, electrical output and mechanical motion. More loads it requires to handle, the slower the completion time for each load.

For example, during the time it requires for the control system 3002 to adjust the current or voltage to nozzle 1008 or 1010 based on the last reflectivity recorded by the end-point detector 1006, wafer 1002 has rotated and moved further away from the original location of the recorded reflectivity, or wafer 1002 is polished for a longer increment as the result of a longer response time required for the adjustment.

In the present exemplary embodiment, distributed sub-control system arrangements is added to the single control system platform and offload the task-oriented functions to individual sub systems, such as a motion server block controller. With reference now to Fig. 4, one sub-control system 4006 will be dedicated to one process chamber, such as wafer electro-polishing module 4008.

The distributive sub system arrangement will automatically solve the problem of the time lagged during polishing process application in a single control system computing. A PC based control system 4002 receives and sends data to each of the sub-control systems 4006 using a device-to-device transmission media 4004 such as RS-485 or DeviceNet.

For example, each sub-control system 4006 will perform same set of tasks for its wafer electro-polishing module 4008. As depicted in Fig. 4, sub-control system 1 will be dedicated to operate the chuck, motor drives, nozzles and end-point detector and to

process the data for digital IO and analog IO for process chamber 1. Simultaneously, the other sub-control systems 2 and 3 will be dedicated to the respective process module for electro-polishing.

Under the distributive arrangement, each sub-control system 4006 will be able to exert better and finer control in both mechanical and electrical performance, i.e., to record both rotational angle and location of wafer 1002 with remaining copper layer and to control nozzle functions based on the reflectivity recorded for the given location in 4 milliseconds or better. Since each sub control system 4006 has sufficient processing capacity, the present exemplary invention can add or extrapolate other values or tables in the recipe based on the reflectivity data to achieve finer control of the polishing.

Moreover, as the result of distributing processing requirement of the wafer electro-polishing to each sub control system 4006, the control system 4002 and the sub control system 4006 will have more available processing power to operate or perform other tasks. In particular, the present invention will make it possible for additional tools and/or applications to be added to the polishing process without diminishing the speed or practicality of such tool configuration. For example, an inline metrology tool can be added to measure the profile of each wafer before said wafer is loaded to the wafer electro-polishing module. The inline metrology tool measures the thickness of metal layer on wafer 1002 for the sub control system 4006 (or control system 4008) to determine the required current output to achieve a flat uniform copper surface. Sub control system 4006 (or control system 4008) then generates a new table with data such as the distance versus current rate times user defined set-points.

Although the present invention has been described with respect to certain embodiments, examples, and applications, it will be apparent to those skilled in the art that various modifications and changes may be made without departing from the invention.

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Title: METHOD FOR ELECTROPOLISHING METAL FILM ON SUBSTRATE
Inventor: Hui WANG et al.
Filed: Herewith
Sheet 1 of 4

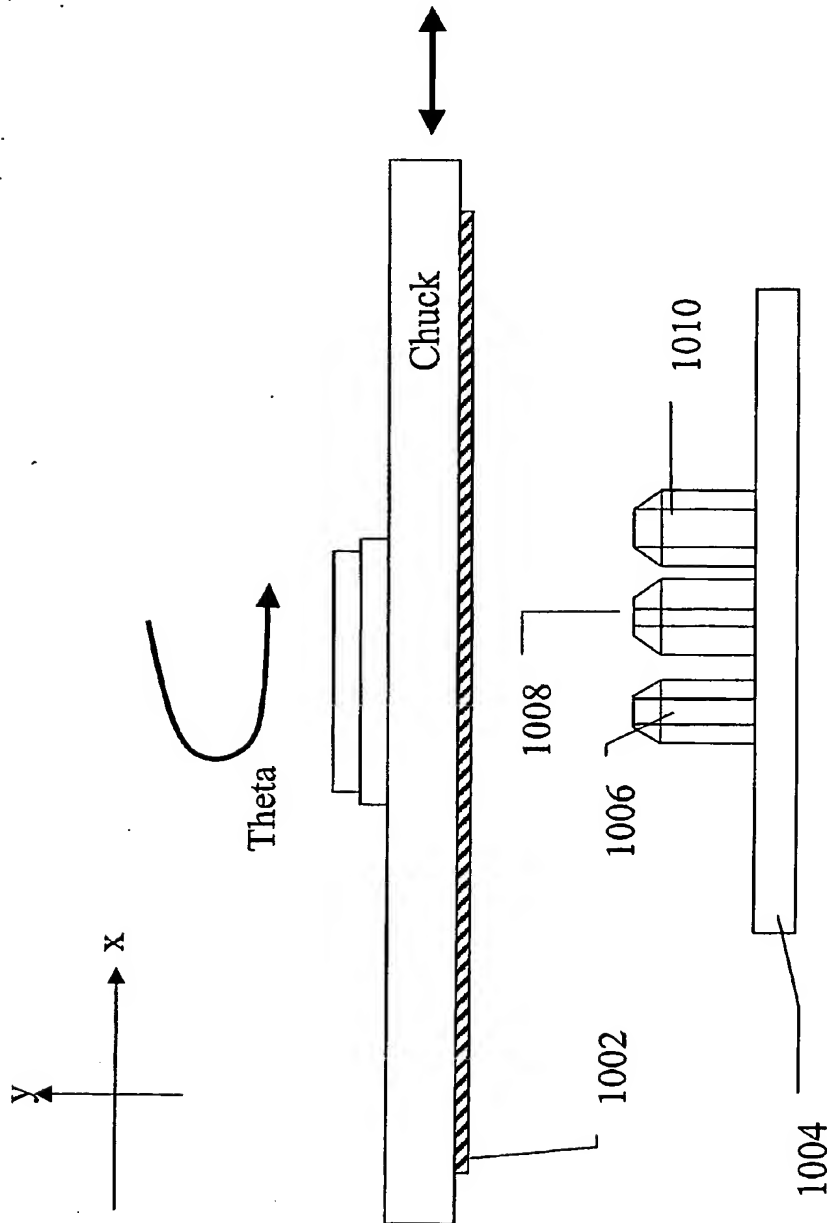


Fig. 1 – Nozzle Plate

5039794, 07/2003

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 Inventor: Hui WANG et al.
 Filed: Herewith
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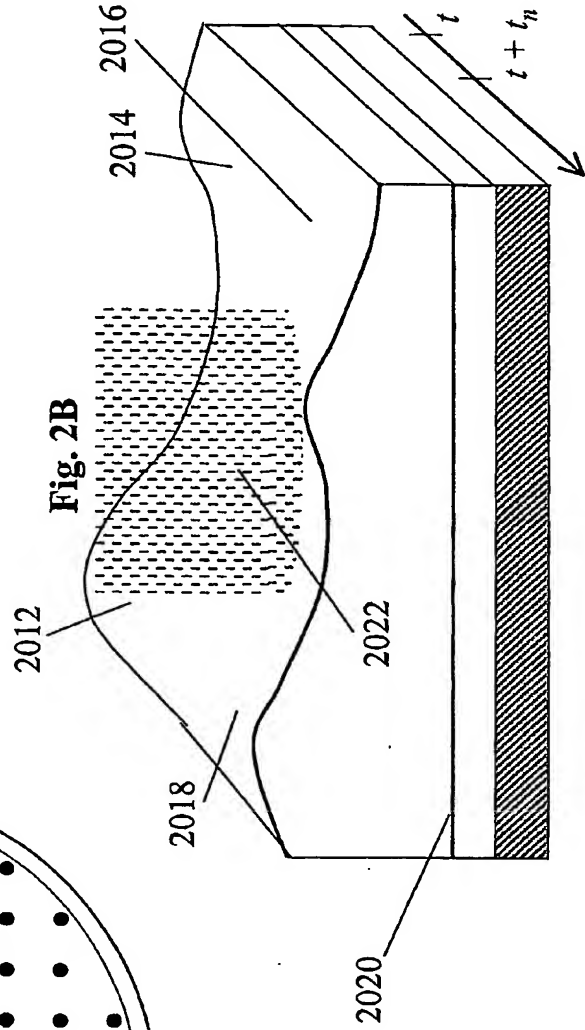
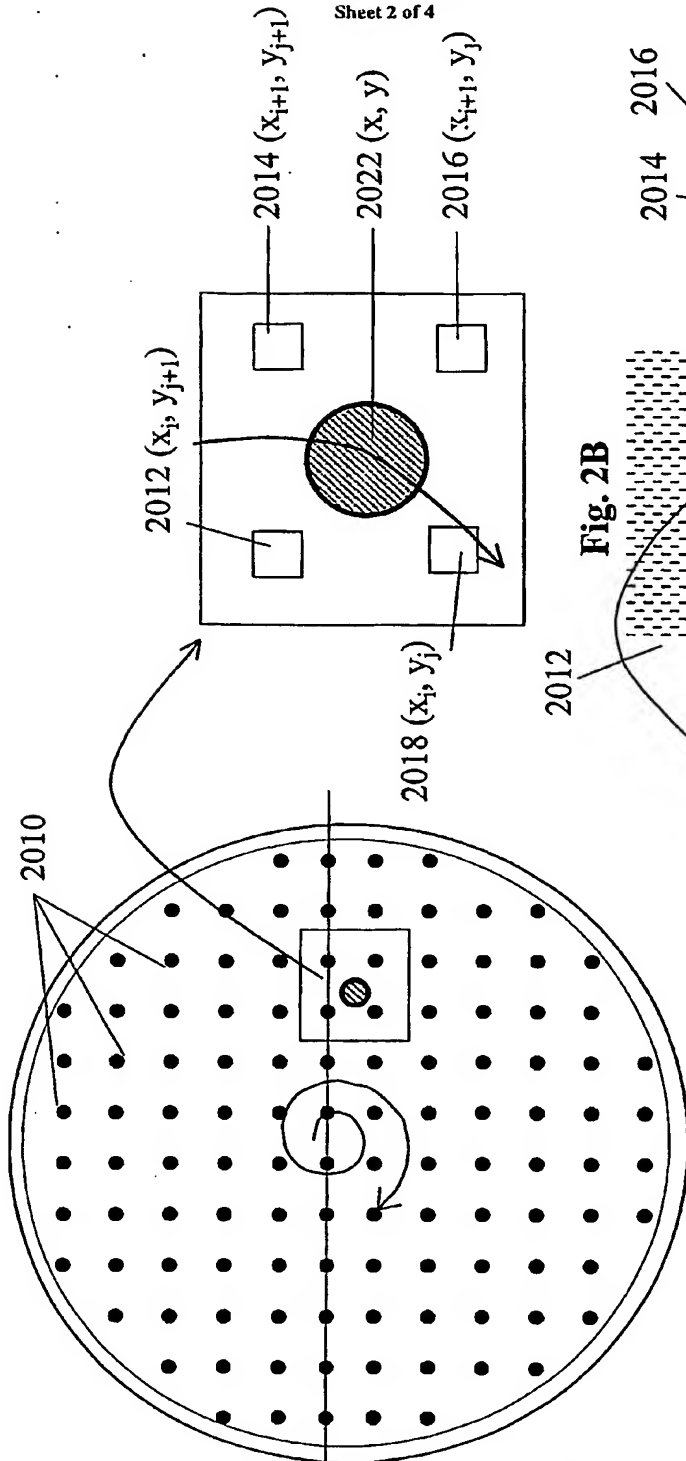


Fig. 2A

Fig. 2C

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Inventor: Hui WANG et al.
Filed: Herewith
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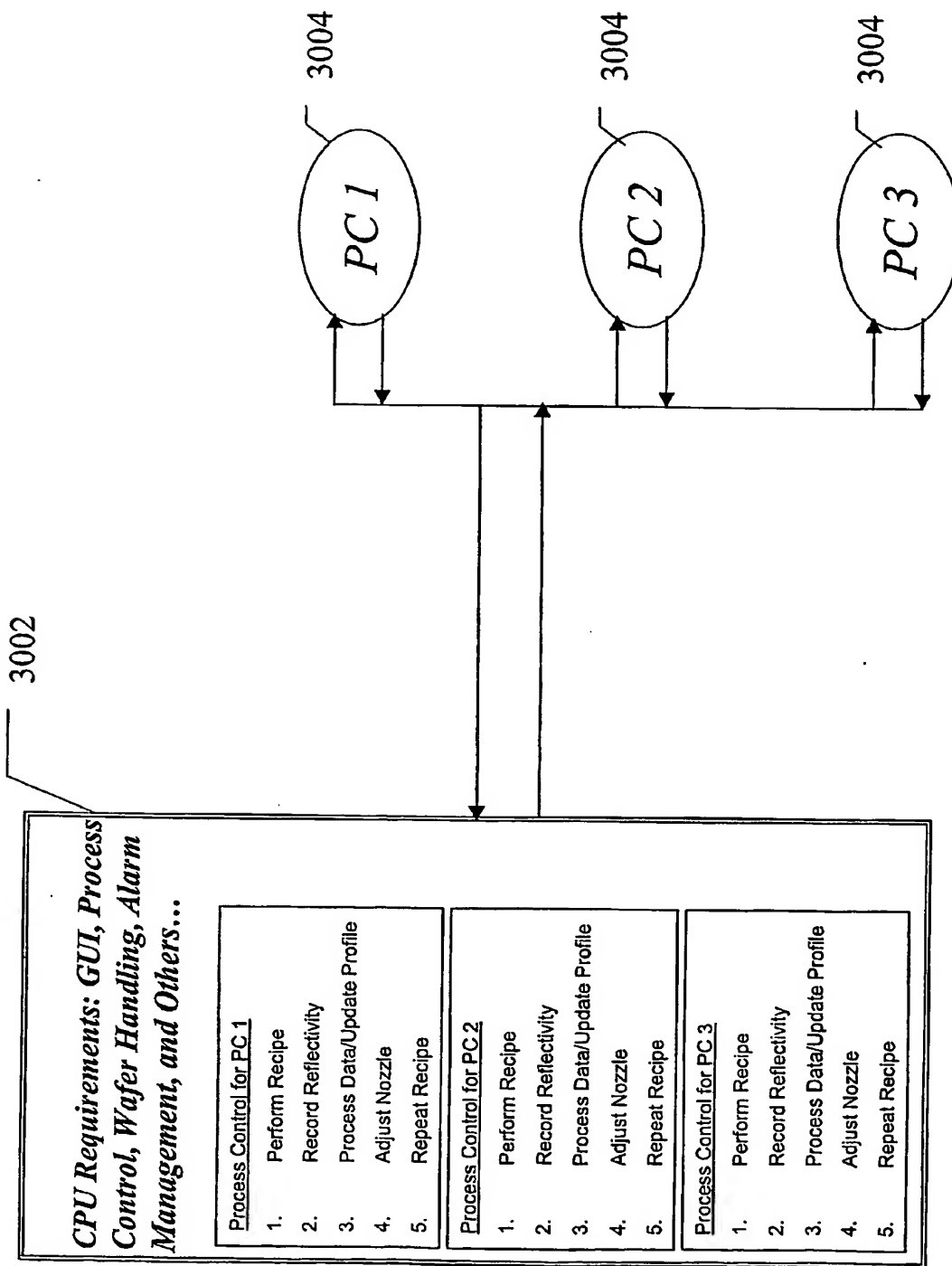


Fig. 3 – Single Control System Platform

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 Inventor: Hui WANG et al.
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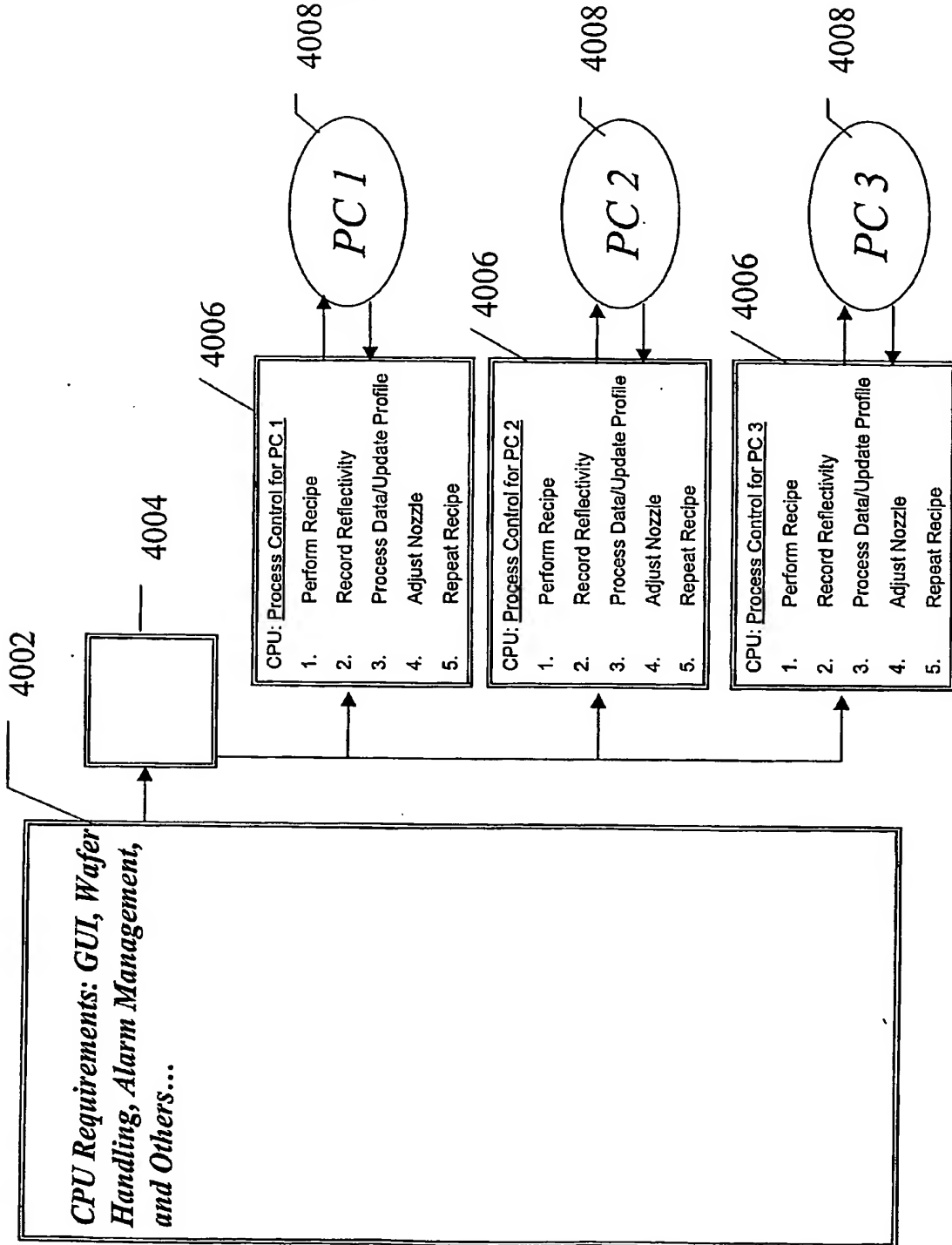


Fig. 4 – Distributed Sub-Control System

WO 2004/010477 A2



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